



RoHS P

S3D50065D1 S3D50065G S3D50065H 650V SIC POWER SCHOTTKY RECTIFIERS

Description

This 650V 50A diode is a high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S3D50065D1/S3D50065G/S3D50065H are ideal for energy sensitive, high frequency applications in challenging environments.

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- "-A" is an AEC-Q101 qualified device
- Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

S3D50065D1	S3D50065G	S3D50065H
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177	K 2	
///	1	1 2
		TO 04740
TO-247AD		TO-247AC
TO-247-3	(TO-263-2)	TO-247-2
PIN 10-NC	PIN 1 ()	
PIN 20 O CASE	PIN 2 O	-O CASE

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vdc	-	650	V
Average Rectified Forward Current	I _{F (AV)1}	T _c =25°C	112	A
Average Rectilica Folward Ourient	IF (AV)2	T _c =137°C	50	A
	I _{FRM1}	10ms, Half Sine pulse, T_C =25°C	121	А
Repetitive Peak Forward Surge Current	I _{FRM2}	10ms, Half Sine pulse, T _C =110°C	68	A
	I _{FSM1}	10ms, Half Sine pulse, T _C =25°C	300	А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM2}	10ms, Half Sine pulse, T_C =110°C	209	A

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Data Sheet N2450, REV.B

Electrical Characteristics:





Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	V _{F1} @ 50A, Pulse, T _J = 25 °C		1.7	V
	VF2	@ 50A, Pulse, T _J = 175 °C	2.2	2.4	V
Reverse Current at DC condition*	I _{R1}	$@V_R = rated V_R$ T _J = 25 °C	1	40	uA
Reverse Current *	I _{R2}	$@V_R = rated V_R$ T _J = 175 °C	10	60	uA
Junction Capacitance	Ст	V _R =0V, T _J =25℃,f=100MHz	3120	-	pF
Reverse Recovery Charge	Qc	I _F = 50A, di/dt = 200A/μs V _R = 400 V, T _J =25°C	193.4	-	nC
Capacitance Stored Energy	Ec	V _R = 400 V, T _J =25°C	47.37	-	μJ

* Pulse width < 300 µs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	S3D50065G	S3D50065D1	S3D50065H	Units
Junction Temperature	TJ	-	-55 to +175		°C	
Storage Temperature	T _{stg}	-	-55 to +175		°C	
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation	0.75	0.70(per leg) 0.35(both leg)	0.76	°C/W

Ordering Information

Device	Package	Shipping
S3D50065D1	TO-247AD(TO-247-3)	25pcs /tube
S3D50065G	D2PAK(TO-263-2)	800pcs /reel
S3D50065H	TO-247AC(TO-247-2)	25pcs /tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.







Ratings and Characteristics Curves

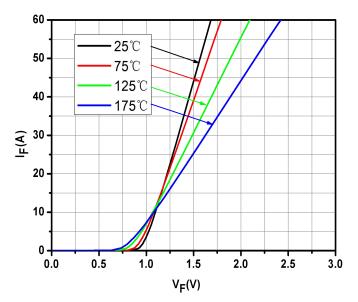


Fig.1-Typical Forward Voltage Characteristics

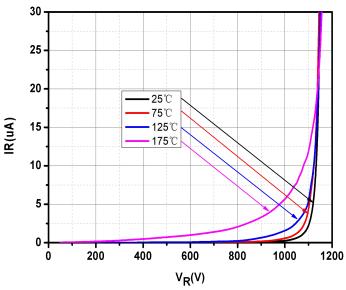


Fig.2-Typical Reverse Characteristics

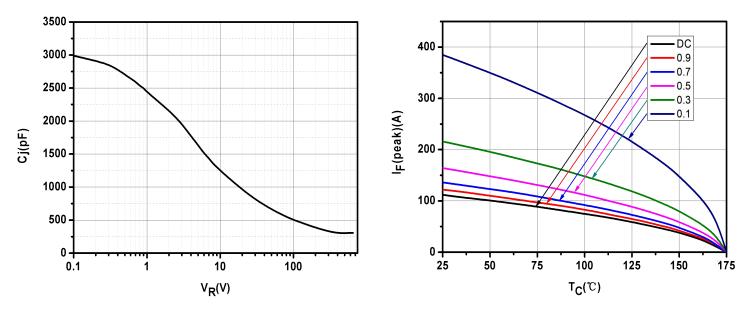


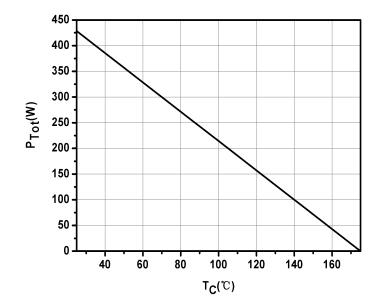
Fig.3-Capacitance vs. Reverse Voltage

Fig.4-Current Derating









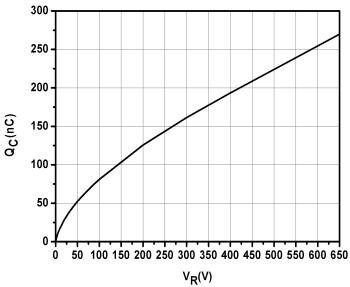


Fig.5-Power Derating

Fig.6-Total Capacitance Charge vs. Reverse Voltage

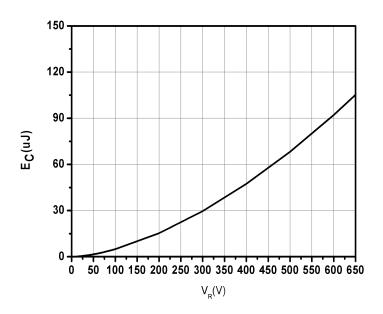
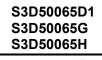


Fig.7-Capacitance Stored Energy



Marking Diagram

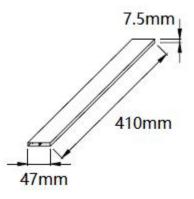


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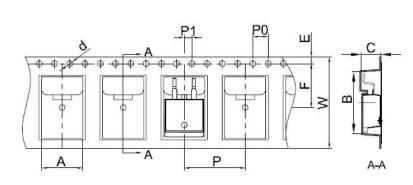
Pb



Tube Specification (TO-247-3/TO-247-2)



Carrier Tape & Reel Specification



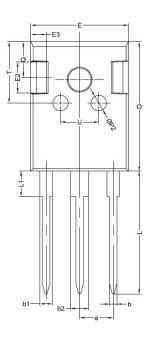
SYMBOL	Millimeters		
STWIDOL	Min.	Max.	
A	10.70	10.90	
В	16.03	16.23	
С	5.11	5.31	
d	1.45	1.65	
E	1.65	1.85	
F	11.40	11.60	
P0	3.90	4.10	
Р	15.90	16.10	
P1	1.90	2.10	
W	23.90	24.30	

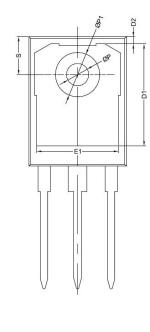




S3D50065D1

Mechanical Dimensions TO-247AD

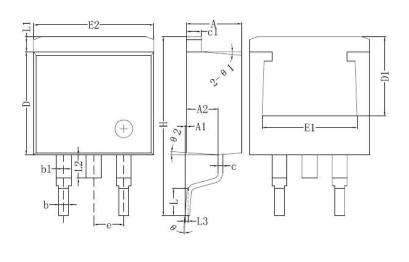




CYMPOL	Millimeters			
SYMBOL	MIN.	TYP.	MAX.	
A	4.80		5.20	
A1	2.00		2.75	
A2	1.90		2.10	
b	1.00		1.40	
b1	1.80		2.40	
b2	2.80		3.40	
с	0.40		0.75	
D	19.80		21.20	
D1		16.55		
D2 E		1.20		
E	15.20		16.00	
E1		13.30		
E2 E3		5.00		
E3		2.50		
е	5.20		5.70	
L	13.90		20.70	
L1	3.70		4.30	
Р	3.50		3.70	
P1	7.1		7.40	
P2		2.50		
Q		5.80		
Q S T	6.05		6.25	
Т		10.00		
U		6.20		

Mechanical Dimensions D²PAK(TO-263-2)

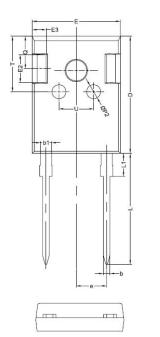
A1

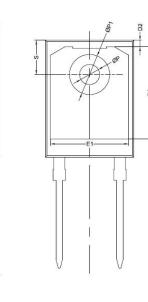


Symbol	Dimensions in millimeters		
	Min.	Max.	
A	4.06	4.83	
A1	0	0.26	
b	0.51	0.99	
b1	1.14	1.78	
С	0.31	0.74	
c1	1.14	1.65	
D	8.38	9.65	
D1	6.4		
E1	6.22		
E2	9.65	10.67	
е	2.54	BSC	
Н	14.6	15.88	
L	1.78	2.8	
L1	-	1.68	
L2	-	2.2	
L3	0.255BSC		
Θ	0	8°	









	Millimeters			
SYMBOL	MIN.	TYP.	MAX.	
A	4.80	5.00	5.20	
A1	2.20	2.41	2.61	
A2	1.90	2.00	2.10	
b	1.10	1.20	1.35	
b1	1.80	2.00	2.20	
С	0.50	0.60	0.75	
D	20.30	21.00	21.20	
D1		16.58		
D2 E		1.17		
E	15.60	15.80	16.00	
E1		14.02		
E2		5.00		
E3		2.50		
е		5.44		
L	19.42	19.92	20.42	
L1		4.13		
Р	3.50	3.60	3.70	
P1	7.1	7.19	7.40	
P2		2.50		
Q		5.80		
Q S	6.05	6.15	6.25	
T		10.00		
U		6.20		

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